Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application. Please amend claims 80, 81, 88, 89, 97, 98, 100, 101, 109 and 110 as follows:

Listing of Claims:

1-79. (Cancelled)

80. (Currently Amended) A method of treating a wafer, comprising:

depositing a first conductive layer onto the wafer;

exposing the wafer in situ to a reducing environment;

depositing a second conductive layer; and

exposing the wafer to a material selected from the group consisting of ~~phosphine, HCL, and boron trichloride,~~ diborane and HCl, wherein the first conductive layer comprises hemispherical silicon grain and wherein the second conductive layer comprises tungsten nitride.

81. (Currently Amended) A method of treating a wafer, comprising:

depositing a first conductive layer onto the wafer;

exposing the wafer in situ to a reducing environment;

depositing a second conductive layer; and

exposing the wafer to a material selected from the group consisting of ~~phosphine, HCL, and boron trichloride,~~ diborane and HCl, wherein the first conductive layer comprises tungsten nitride and wherein the second conductive layer comprises polysilicon.

82. (Previously Presented) The method of claim 80 further comprising forming a third conductive layer on the second conductive layer.

83. (Previously Presented) The method of claim 82 further comprising forming a borophosphosilicate glass layer on the third conductive layer.

84. (Previously Presented) The method of claim 83 wherein the first conductive layer comprises hemispherical silicon grain, the second conductive layer comprises tungsten nitride, and the third conductive layer comprises polysilicon.

85-87. (Cancelled)

88. (Currently Amended) A method of treating a wafer, comprising:

depositing a first conductive layer onto the wafer;

exposing the wafer to a reducing environment;

depositing a second conductive layer; and

passivating at least one of the first and second conductive layers by exposing the wafer to a material selected from the group consisting of diborane~~, phosphine, HCL,~~ and HCl, ~~boron trichloride~~ wherein the first conductive layer comprises hemispherical silicon grain and wherein the second conductive layer comprises tungsten nitride.

89. (Currently Amended) A method of treating a wafer, comprising:

depositing a first conductive layer onto the wafer;

exposing the wafer to a reducing environment;

depositing a second conductive layer; and

passivating at least one of the first and second conductive layers by exposing the wafer to a material selected from the group consisting of diborane~~, phosphine, HCL,~~ and HCl, ~~boron trichloride~~ wherein the first conductive layer comprises tungsten nitride and wherein the second conductive layer comprises polysilicon.

90. (Previously Presented) The method of claim 88 further comprising forming a third conductive layer on the second conductive layer.

91. (Previously Presented) The method of claim 90 further comprising forming a borophosphosilicate glass layer on the third conductive layer.

92. (Previously Presented) The method of claim 91 wherein the first conductive layer comprises hemispherical silicon grain, the second conductive layer comprises tungsten nitride, and the third conductive layer comprises polysilicon.

93. (Previously Presented) The method of claim 81 further comprising forming a third conductive layer on the second conductive layer.

94. (Previously Presented) The method of claim 93 further comprising forming a borophosphosilicate glass layer on the third conductive layer.

95. (Previously Presented) The method of claim 94 wherein the first conductive layer comprises hemispherical silicon grain, the second conductive layer comprises tungsten nitride, and the third conductive layer comprises polysilicon.

96. (Previously Presented) The method of claim 81 wherein exposing the wafer in situ to a reducing environment comprises exposing the wafer to silane gas.

97. (Currently Amended) The method of claim 81 wherein exposing the wafer to a material selected from the group consisting of ~~phosphine and boron trichloride~~ diborane and HCl comprises exposing the wafer to this selection prior to exposing the wafer in situ to a reducing environment.

98. (Currently Amended) The method of claim 81 wherein exposing the wafer to a material selected from the group consisting of ~~phosphine HCL, and boron trichloride~~ diborane and HCl comprises exposing the wafer to this selection prior to depositing the second conductive layer.

99. (Previously Presented) The method of claim 80 wherein exposing the wafer in situ to a reducing environment comprises exposing the wafer to silane gas.

100. (Currently Amended) The method of claim 80 wherein exposing the wafer to a material selected from the group consisting of ~~phosphine and boron trichloride~~ diborane and HCl comprises exposing the wafer to this selection prior to exposing the wafer in situ to a reducing environment.

101. (Currently Amended) The method of claim 80 wherein exposing the wafer to a material selected from the group consisting of ~~phosphine HCL, and boron trichloride~~ diborane and HCl comprises exposing the wafer to this selection prior to depositing the second conductive layer.

102. (Previously Presented) The method of claim 89 further comprising forming a third conductive layer on the second conductive layer.

103. (Previously Presented) The method of claim 102 further comprising forming a borophosphosilicate glass layer on the third conductive layer.

104. (Previously Presented) The method of claim 103 wherein the first conductive layer comprises hemispherical silicon grain, the second conductive layer comprises tungsten nitride, and the third conductive layer comprises polysilicon.

105. (Previously Presented) The method of claim 89 wherein exposing the wafer to a reducing environment comprises exposing the wafer to silane gas.

106. (Previously Presented) The method of claim 89 wherein exposing the wafer to a material selected from the group consisting of diborane, phosphine, HCL, and boron trichloride comprises exposing the wafer to this selection prior to exposing the wafer to a reducing environment.

107. (Previously Presented) The method of claim 89 wherein exposing the wafer to a material selected from the group consisting of diborane, phosphine, HCL, and boron trichloride comprises exposing the wafer to this selection prior to depositing the second conductive layer.

108. (Previously Presented) The method of claim 88 wherein exposing the wafer to a reducing environment comprises exposing the wafer to silane gas.

109. (Currently Amended) The method of claim 88 wherein exposing the wafer to a material selected from the group consisting of diborane, ~~phosphine, HCL,~~ and HCl ~~boron trichloride~~ comprises exposing the wafer to this selection prior to exposing the wafer to a reducing environment.

110. (Currently Amended) The method of claim 88 wherein exposing the wafer to a material selected from the group consisting of diborane, ~~phosphine, HCL,~~ and HCl ~~boron trichloride~~ comprises exposing the wafer to this selection prior to depositing the second conductive layer.